

NTZD3154N

Small Signal MOSFET

20 V, 540 mA, Dual N-Channel

Features

- Low $R_{DS(on)}$ Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These are Pb-Free Devices

Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	20	V	
Gate-to-Source Voltage		V_{GS}	± 6.0	V	
Continuous Drain Current (Note 1)	Steady State	I_D	$T_A = 25^\circ\text{C}$	540	mA
			$T_A = 85^\circ\text{C}$	390	
Power Dissipation (Note 1)	Steady State	P_D	250	mW	
Continuous Drain Current (Note 1)	$t \leq 5$ s	I_D	$T_A = 25^\circ\text{C}$	570	mA
			$T_A = 85^\circ\text{C}$	410	
Power Dissipation (Note 1)	$t \leq 5$ s	P_D	280	mW	
Pulsed Drain Current	$t_p = 10$ μs	I_{DM}	1.5	A	
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	350	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)		447	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

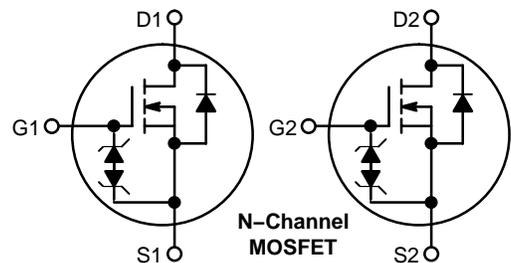
1. Surface mounted on FR4 board using 1 in sq pad size (Cu. area = 1.127 in sq [1 oz] including traces).



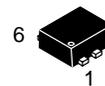
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max (Note 1)
20	400 m Ω @ 4.5 V	540 mA
	500 m Ω @ 2.5 V	
	700 m Ω @ 1.8 V	



N-Channel MOSFET



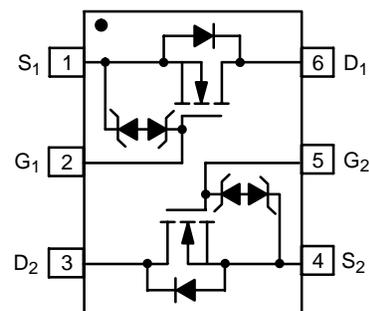
SOT-563-6
CASE 463A

MARKING DIAGRAM



TV = Specific Device Code
D = Date Code

PINOUT: SOT-563



Top View

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTZD3154N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20	-	-	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	-	-	14	-	mV/°C	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V V _{DS} = 16 V	T _J = 25°C	-	-	1.0	μA
			T _J = 125°C	-	-	5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V	-	-	±5.0	μA	

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.45	-	1.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	-	-	2.0	-	mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 540 mA	-	0.4	0.55	Ω
		V _{GS} = 2.5 V, I _D = 500 mA	-	0.5	0.7	
		V _{GS} = 1.8 V, I _D = 350 mA	-	0.7	0.9	
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 540 mA	-	1.0	-	S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 16 V	-	80	150	pF
Output Capacitance	C _{OSS}		-	13	25	
Reverse Transfer Capacitance	C _{RSS}		-	10	20	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V; I _D = 540 mA	-	1.5	2.5	nC
Threshold Gate Charge	Q _{G(TH)}		-	0.1	-	
Gate-to-Source Charge	Q _{GS}		-	0.2	-	
Gate-to-Drain Charge	Q _{GD}		-	0.35	-	

SWITCHING CHARACTERISTICS, V_{GS} = V (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 540 mA, R _G = 10 Ω	-	6.0	-	ns
Rise Time	t _r		-	4.0	-	
Turn-Off Delay Time	t _{d(OFF)}		-	16	-	
Fall Time	t _f		-	8.0	-	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 350 mA	T _J = 25°C	-	0.7	1.2	V
			T _J = 125°C	-	0.6	-	
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _{SD} /dt = 100 A/μs, I _S = 350 mA	-	6.5	-	ns	

2. Surface-mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).
3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

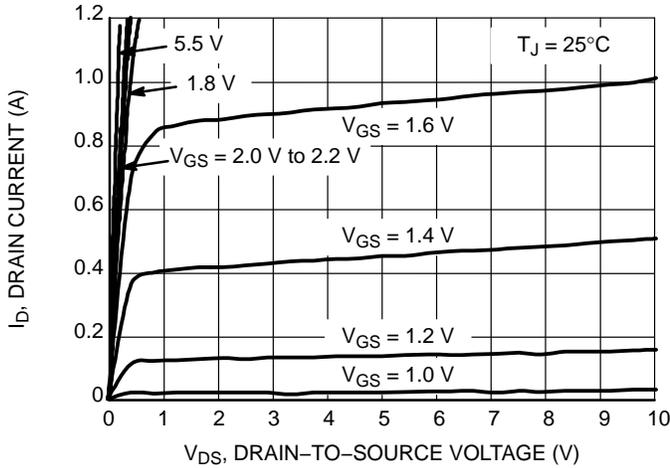


Figure 1. On-Region Characteristics

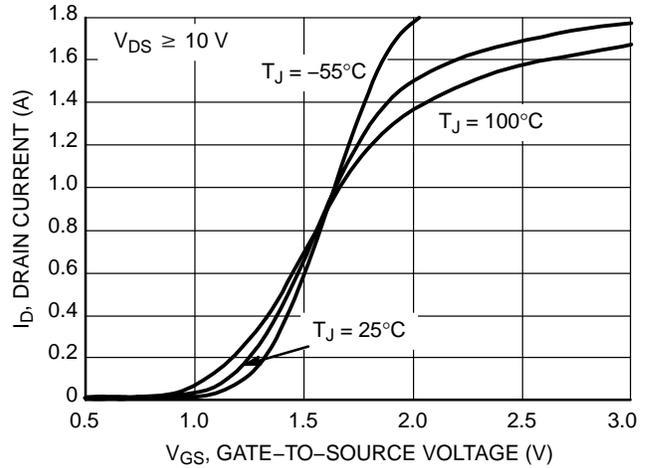


Figure 2. Transfer Characteristics

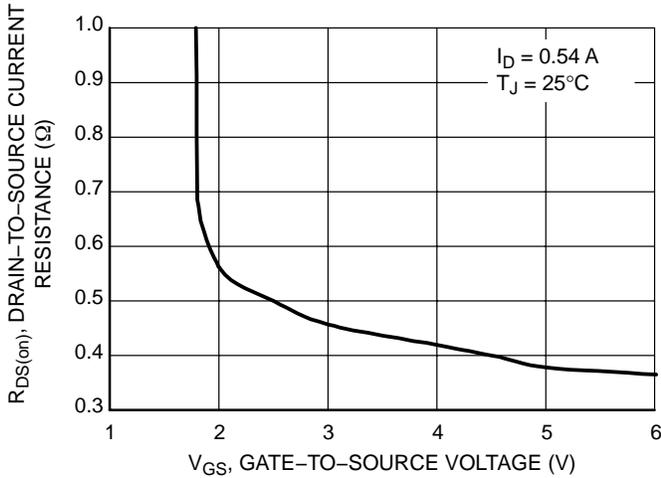


Figure 3. On-Resistance versus Gate-to-Source Voltage

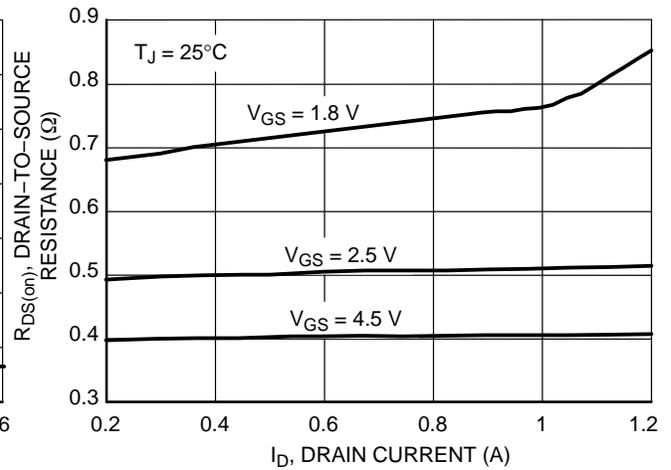


Figure 4. On-Resistance versus Drain Current and Gate Voltage

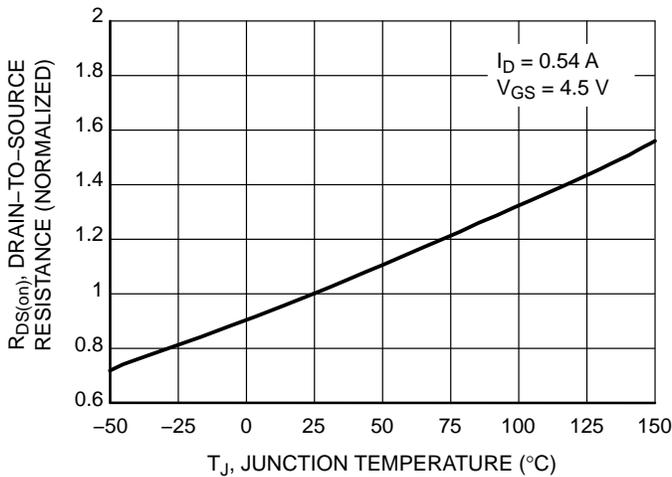


Figure 5. On-Resistance Variation with Temperature

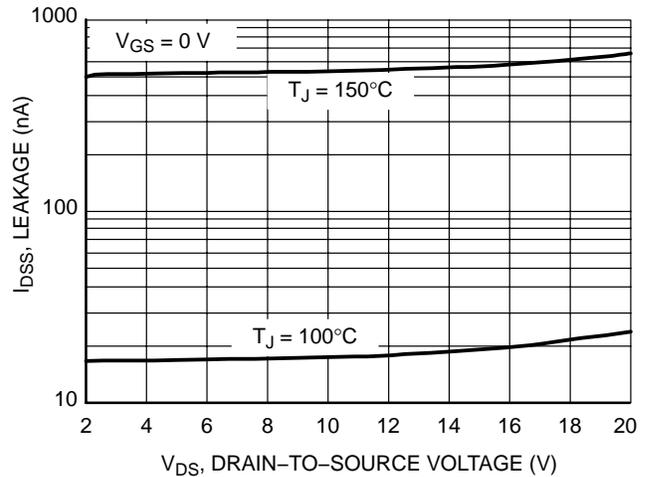


Figure 6. Drain-to-Source Leakage Current versus Voltage

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

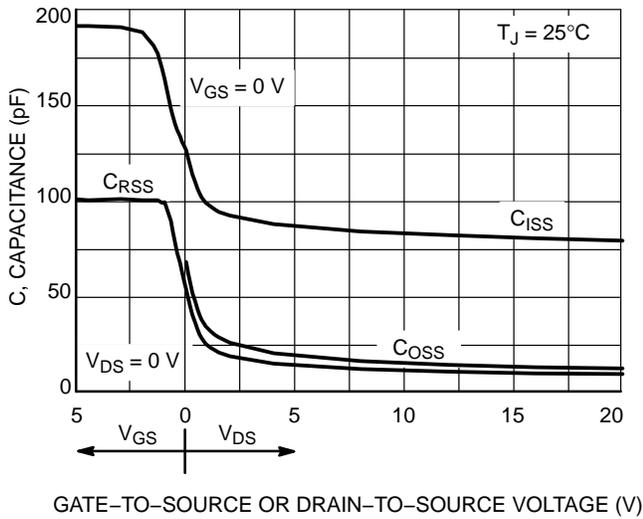


Figure 7. Capacitance Variation

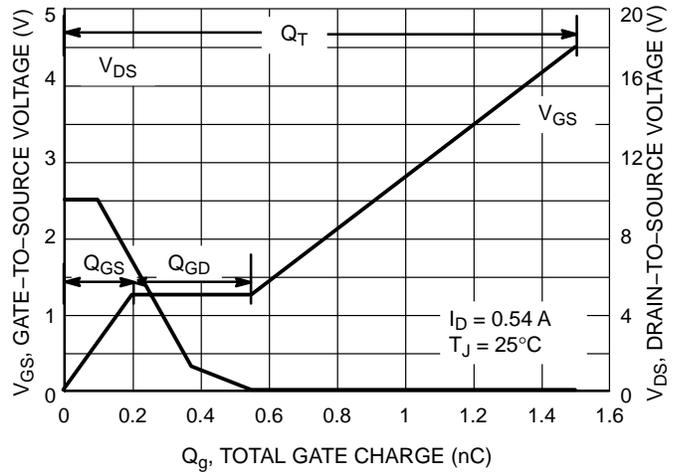


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

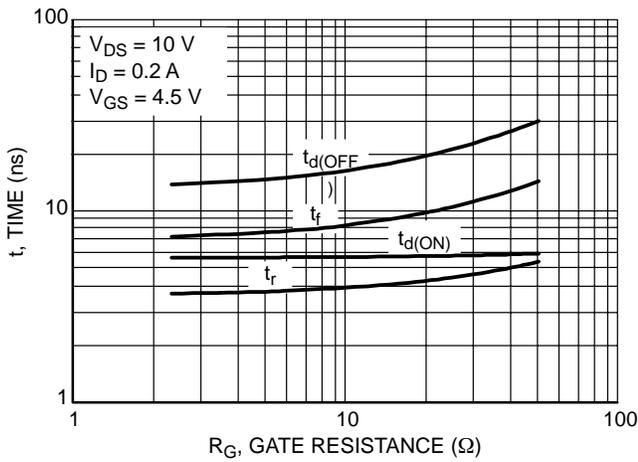


Figure 9. Resistive Switching Time Variation versus Gate Resistance

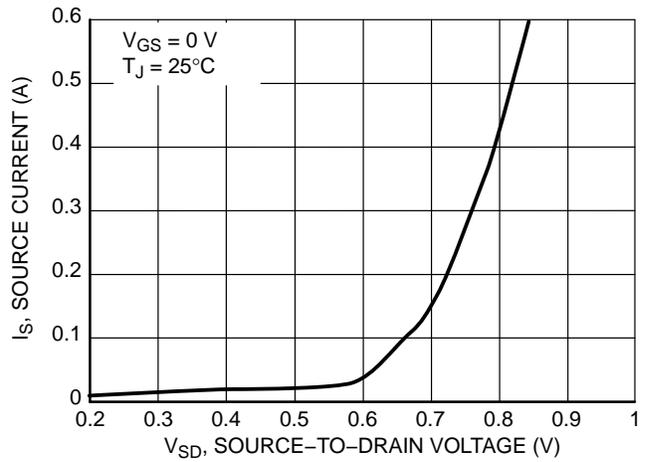


Figure 10. Diode Forward Voltage versus Current

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ORDERING INFORMATION

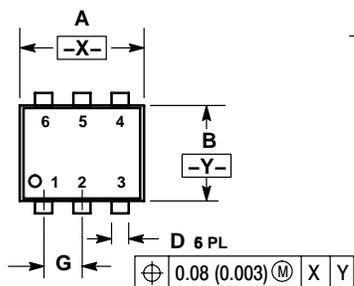
Device	Package	Shipping
NTZD3154NT1G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZD3154NT5G	SOT-563 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

SOT-563, 6 LEAD
CASE 463A-01
ISSUE D

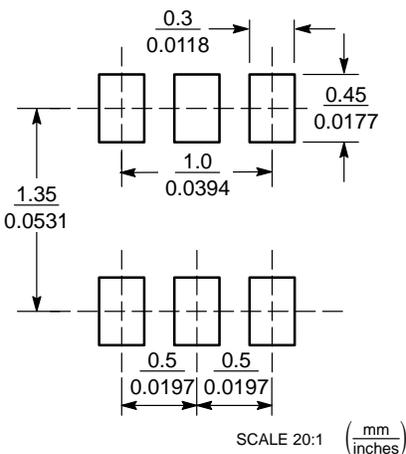


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.50	1.70	0.059	0.067
B	1.10	1.30	0.043	0.051
C	0.50	0.60	0.020	0.024
D	0.17	0.27	0.007	0.011
G	0.50 BSC		0.020 BSC	
J	0.08	0.18	0.003	0.007
K	0.10	0.30	0.004	0.012
S	1.50	1.70	0.059	0.067

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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